

ESDAxxSC5 ESDAxxSC6 QUAD TRANSIL™ ARRAY FOR ESD PROTECTION

Application Specific Discretes A.S.D.™

APPLICATIONS

Where transient overvoltage protection in ESD sensitive equipment is required, such as :

-COMPUTERS

- PRINTERS
- COMMUNICATION SYSTEMS
- GSM HANDSETS AND ACCESSORIES
- OTHER TELEPHONE SET

FEATURES

- 4 UNIDIRECTIONAL TRANSILTM FUNCTIONS
- LOW LEAKAGE CURRENT: I_R max. < 20 μA</p>
- 300 W PEAK PULSE POWER (8/20 µs)

DESCRIPTION

The ESDAxxSC5 and ESDAxxSC6 are monolithic voltage suppressors designed to protect components which are connected to data and transmission lines against ESD.

They clamp the voltage just above the logic level supply for positive transients, and to a diode drop below ground for negative transient.

BENEFITS

High ESD protection level : up to 25 kV High integration Suitable for high density boards

COMPLIES WITH THE FOLLOWING STANDARDS:

IEC 1000-4-2 : level 4

MIL STD 883C-Method 3015-6 : class3 (human body model)



FUNCTIONAL DIAGRAM SOT23-5L



SOT23-6L



ESDAxxSC5 / ESDAxxSC6

Symbol	Test conditions	Value	Unit
Vpp	ESD discharge - MIL STD 883C - Method 3015-6	25	kV
P _{PP}	Peak pulse power (8/20µs) note1	300	W
Tj	Junction temperature	150	°C
T _{stg}	Storage temperature range	-55 to +150	°C
TL	Lead solder temperature (10 second duration)	260	°C
T _{op}	Operating temperature range	-40 to +85	°C

ABSOLUTE MAXIMUM RATINGS (T_{amb} = 25°C)

note 1:500 W for ESDA6V1SC5 AND ESDA6V1SC6

ELECTRICAL CHARACTERISTICS (Tamb = 25°C)

Symbol	Parameter				
Vrm	Stand-off voltage				
V _{BR} Breakdown voltage					
V _{CL}	Clamping voltage				
I _{RM}	Leakage current				
IPP	Peak pulse current				
ατ	Voltage temperature coefficient				
С	Capacitance				
Rd	Dynamic resistance				
V _F Forward voltage drop					



	VBR	@	IR	I _{RM} @	VRM	Rd	αΤ	С	V _F @	〕 F
Types	min.	max.		max.		typ.	max.	typ.	max.	
						note 1	note 2	0V bias		
	V	V	mA	μA	V	mΩ	10 ⁻⁴ /°C	pF	V	mA
ESDA6V1SC5 ESDA6V1SC6	6.1	7.2	1	20	5.25	350	6	190	1.25	200
ESDA14V2SC5 ESDA14V2SC6	14.2	15.8	1	5	12	650	10	100	1.25	200

note 1 : Square pulse, lpp = 15A, tp=2.5 μ s. **note 2** : Δ VBR = α T* (Tamb -25°C) * VBR (25°C)

CALCULATION OF THE CLAMPING VOLTAGE

USE OF THE DYNAMIC RESISTANCE

The ESDA family has been designed to clamp fast spikes like ESD. Generally the PCB designers need to calculate easily the clamping voltage V_{CL} . This is why we give the dynamic resistance in addition to the classical parameters. The voltage across the protection cell can be calculated with the following formula:

 $V_{CL} = V_{BR} + Rd I_{PP}$

Where lpp is the peak current through the ESDA cell.

DYNAMIC RESISTANCE MEASUREMENT

The short duration of the ESD has led us to prefer a more adapted test wave, as below defined, to the classical $8/20\mu s$ and $10/1000\mu s$ surges.



2.5µs duration measurement wave.

As the value of the dynamic resistance remains stable for a surge duration lower than 20µs, the 2.5µs rectangular surge is well adapted. In addition both rise and fall times are optimized to avoid any parasitic phenomenon during the measurement of Rd.

ESDAxxSC5 / ESDAxxSC6

Fig. 1 : Peak power dissipation versus initial junction temperature.



Fig. 3 : Clamping voltage versus peak pulse current (Tj initial = 25 °C). Rectangular waveform tp = 2.5μ s.



Fig. 5: Relative variation of leakage current versus junction temperature (typical values).



Fig. 2 : Peak pulse power versus exponential pulse duration (Tj initial = $25 \degree$ C).



Fig. 4 : Capacitance versus reverse applied voltage (typical values).



Fig. 6 : Peak forward voltage drop versus peak forward current (typical values).



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APPLICATION EXAMPLE : ESD protection by ESDAXXXSCX

Electrostatic discharge (ESD) is a major cause of failure in electronic systems.

Transient Voltage Suppressors (TVS) are an ideal choice for ESD protection. They are capable of clamping the incoming transient overvoltage to a low enough level such that damage to the protected semiconductor is prevented.

They serve as parallel protection elements, connected between the signal line and ground. As the transient rises above the operating voltage of the device, the TVS array becomes a low impedance path diverting the transient current to ground.

Surface mount TVS arrays offer the best choice for minimal lead inductance.



The ESDAxxSCx array is the ideal board level protection of ESD sensitive semiconductor components.

The tiny SOT23-5L and SOT23-6L packages allow design flexibility in the high density boards where the space saving is at a premium. This enables to shorten the routing and contributes to hardening against ESD.

ADVICE FOR OPTIMIZING CIRCUIT BOARD LAYOUT

Circuit board layout is a critical design step in the suppression of ESD induced transients. The following guidelines are recommended :

- The ESDAxxL should be placed as close as possible to the input terminals or connectors.
- The path length between the ESD suppressor and the protected line should be minimized
- All conductive loops, including power and ground loops should be minimized
- The ESD transient return path to ground should be kept as short as possible.
- Ground planes should be used whenever possible.

ESDAxxSC5 / ESDAxxSC6

ORDER CODE



MARKING

Туре	Marking
ESDA6V1SC5	EC61
ESDA6V1SC6	ES61

Packaging: Standard packaging is tape and reel.

PACKAGE MECHANICAL DATA SOT23-5L



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MARKING

Туре	Marking
ESDA14V2SC5	EC15
ESDA14V2SC6	ES15

Packaging: Standard packaging is tape and reel.

	DIMENSIONS						
REF.	Mi	llimete	ers	Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А	0.90		1.45	0.035		0.057	
A1			0.15			0.006	
A2	0.90		1.30	0.035		0.0512	
b	0.35		0.50	0.0137		0.02	
С	0.09		0.20	0.004		0.008	
D	2.80		3.00	0.11		0.118	
Е	1.50		1.75	0.059		0.0689	
е		0.95			0.0374		
Н	2.60		3.00	0.102		0.118	
L	0.10		0.60	0.004		0.024	
М			10°			10°	

PACKAGE MECHANICAL DATA

SOT23-6L



	DIMENSIONS						
REF.	Mi	llimete	ers	Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
Α	0.90		1.45	0.035		0.057	
A1	0		0.15	0		0.006	
A2	0.90		1.30	0.035		0.0512	
b	0.35		0.50	0.0137		0.02	
С	0.09		0.20	0.004		0.008	
D	2.80		3.00	0.11		0.118	
Е	1.50		1.75	0.059		0.0689	
е		0.95			0.0374		
Н	2.60		3.00	0.102		0.118	
L	0.10		0.60	0.004		0.024	
М			10°			10°	

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